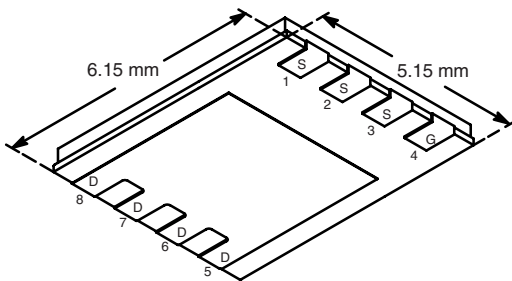


N-Channel 25-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^{a, g}	Q _g (Typ.)
25	0.002 at V _{GS} = 10 V	60	42 nC
	0.0025 at V _{GS} = 4.5 V	60	

PowerPAK® SO-8



Bottom View

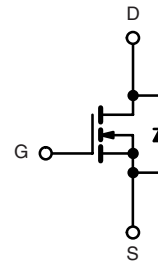
FEATURES

- Halogen-free
- TrenchFET® Power MOSFETs
- 100 % R_g Tested
- 100 % Avalanche Tested



APPLICATIONS

- Low-Side in CPU and GPU core DC/DC
 - Gaming
 - Desktop



N-Channel MOSFET

Ordering Information: Si7194DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	25	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	60 ^{a, g}
		T _C = 70 °C	60 ^{a, g}
		T _A = 25 °C	38 ^{b, c}
		T _A = 70 °C	30 ^{b, c}
Pulsed Drain Current	I _{DM}	80	A
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	
		T _A = 25 °C	4.9 ^{b, c}
Single Pulse Avalanche Current	I _{AS}	50	mJ
Single Pulse Avalanche Energy	E _{AS}	125	
Maximum Power Dissipation	P _D	T _C = 25 °C	83
		T _C = 70 °C	53
		T _A = 25 °C	5.4 ^{b, c}
		T _A = 70 °C	3.4 ^{b, c}
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	t ≤ 10 s	R _{thJA}	18	23	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	1.0	1.5	

Notes:

- Based on T_C = 25 °C.
- Surface Mounted on 1" x 1" FR4 board.
- t = 10 s.
- See Solder Profile (<http://www.vishay.com/ppg?73257>). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under Steady State conditions is 65 °C/W.
- Package Limited.



SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	25			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		23		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 5.7		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.0		2.6	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	30			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		0.0016	0.002	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		0.002	0.0025	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 10\text{ V}, I_D = 20\text{ A}$		120		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		6590		pF
Output Capacitance	C_{oss}			930		
Reverse Transfer Capacitance	C_{rss}			420		
Total Gate Charge	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		95	145	nC
				42	65	
Gate-Source Charge	Q_{gs}	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		16		
Gate-Drain Charge	Q_{gd}			9.7		
Gate Resistance	R_g	$f = 1\text{ MHz}$	0.2	0.9	1.8	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}, R_L = 1\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		19	35	ns
Rise Time	t_r			8	16	
Turn-Off Delay Time	$t_{d(off)}$			47	90	
Fall Time	t_f			9	18	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}, R_L = 1\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		46	85	
Rise Time	t_r			25	45	
Turn-Off Delay Time	$t_{d(off)}$			72	130	
Fall Time	t_f			40	70	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			60	A
Pulse Diode Forward Current ^a	I_{SM}				80	
Body Diode Voltage	V_{SD}	$I_S = 4\text{ A}$		0.73	1.1	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 10\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		41	80	ns
Body Diode Reverse Recovery Charge	Q_{rr}			43	90	nC
Reverse Recovery Fall Time	t_a			21		ns
Reverse Recovery Rise Time	t_b			20		

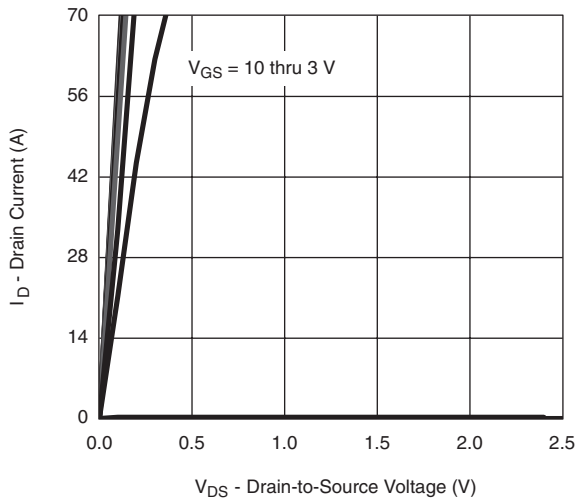
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

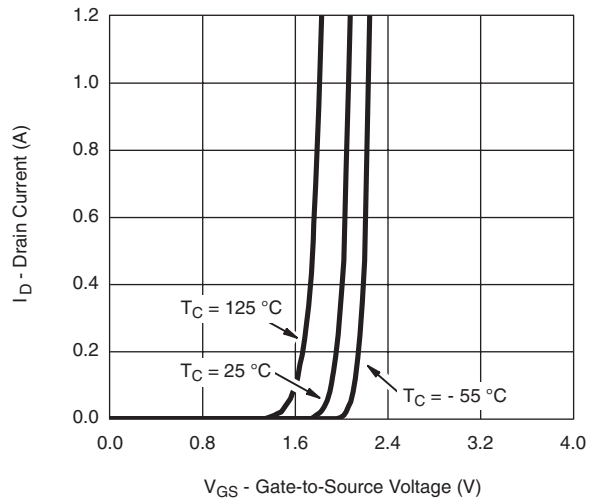
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



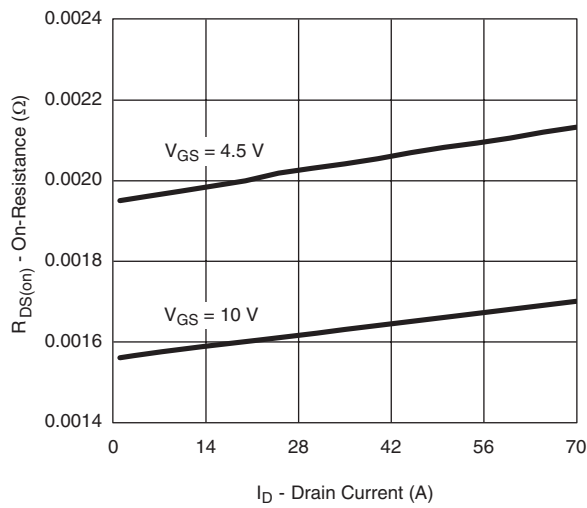
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



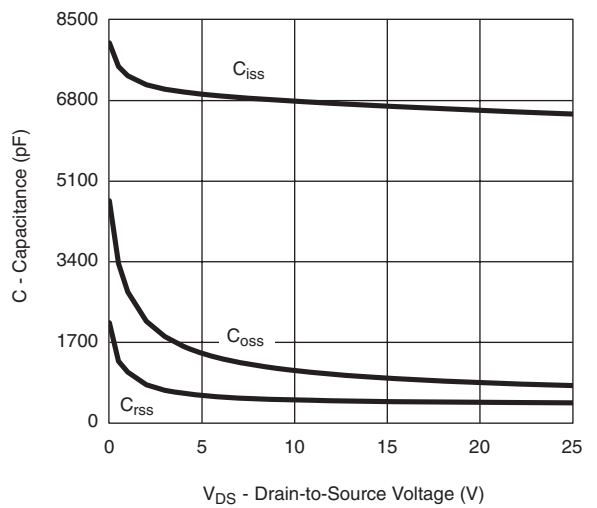
Output Characteristics



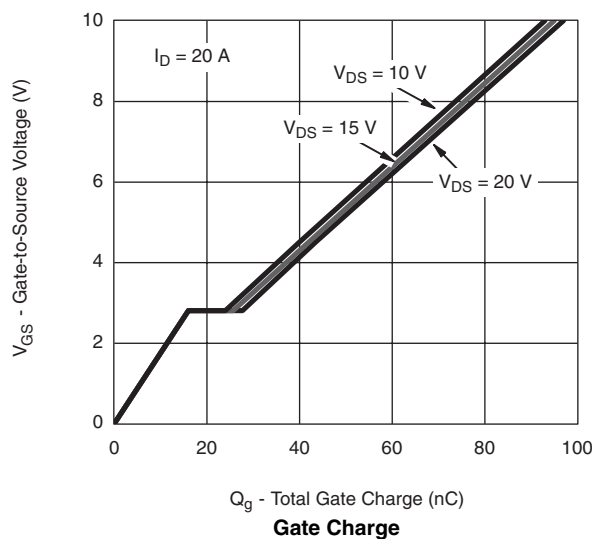
Transfer Characteristics



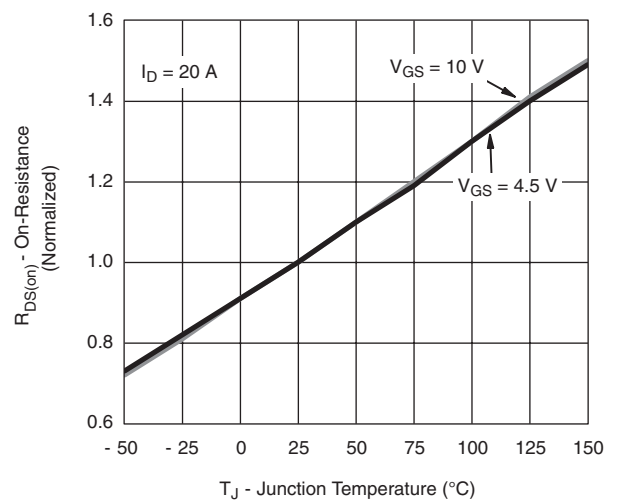
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



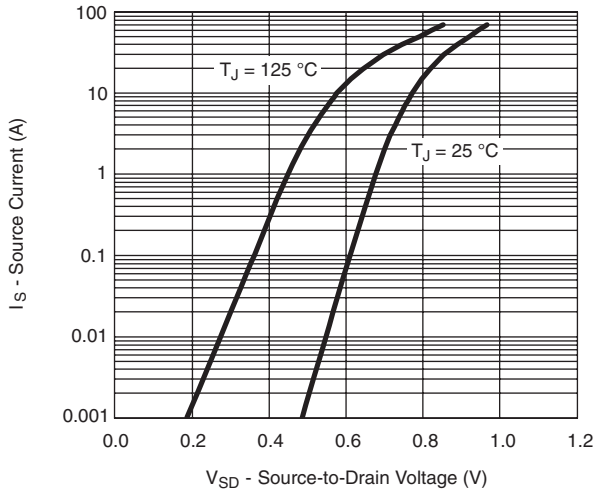
Gate Charge



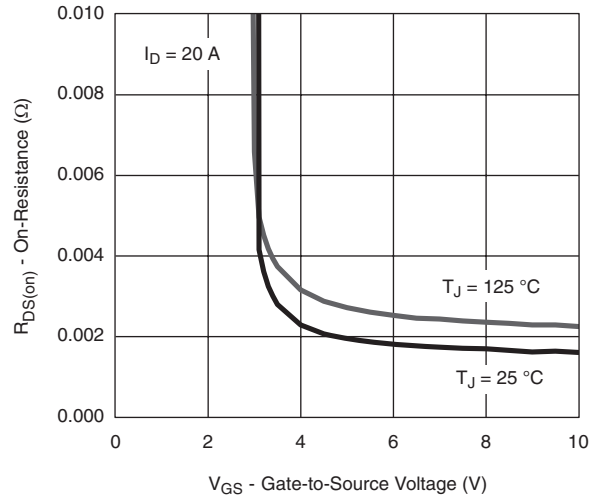
On-Resistance vs. Junction Temperature



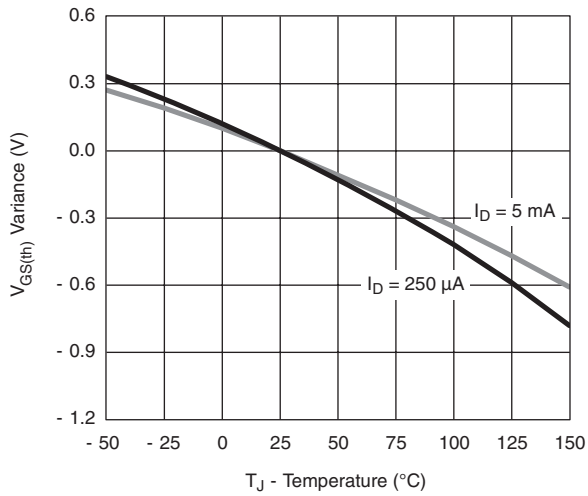
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



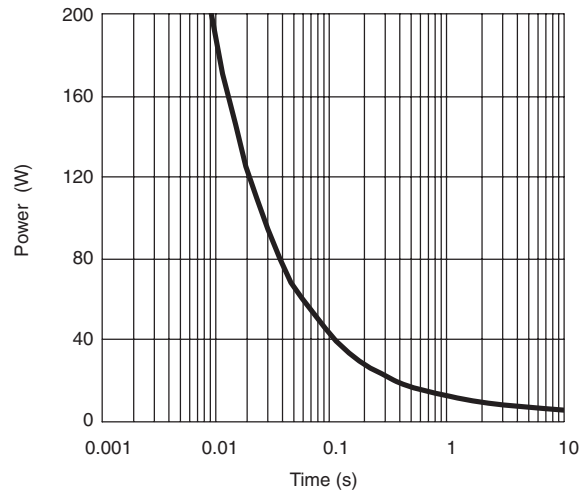
Source-Drain Diode Forward Voltage



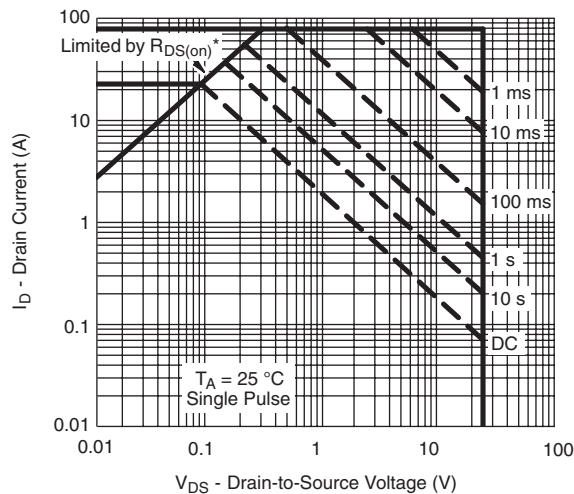
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient

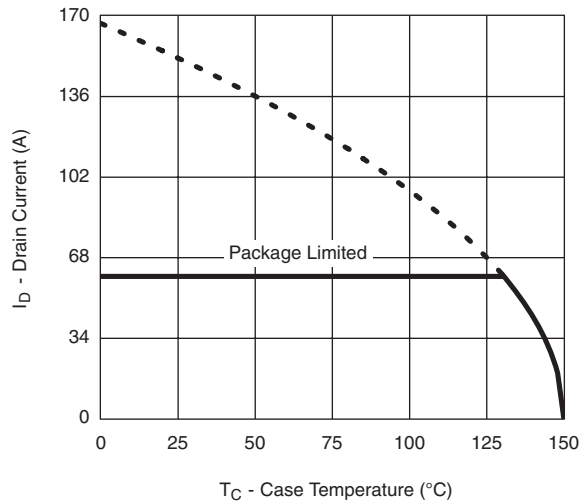


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

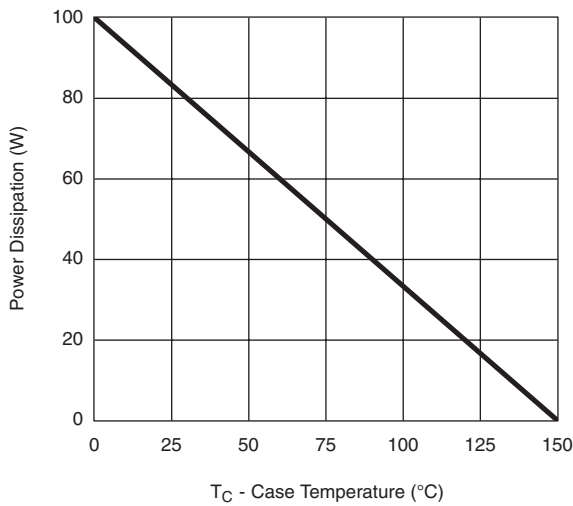
Safe Operating Area, Junction-to-Ambient



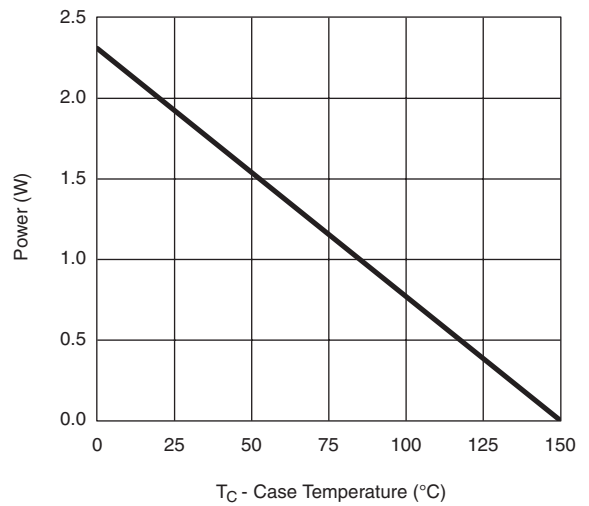
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Current Derating*



Power, Junction-to-Case

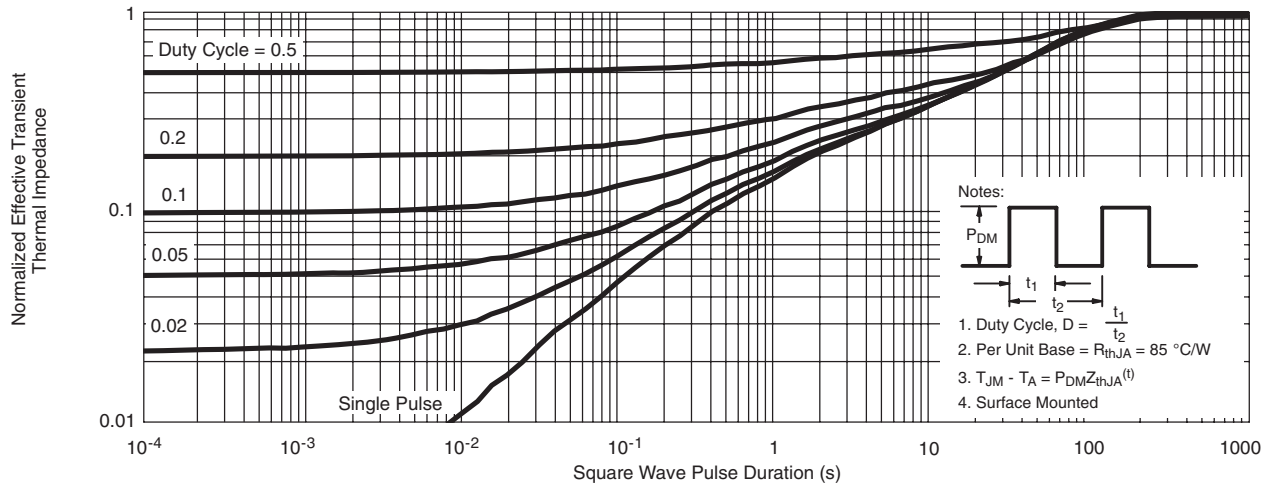


Power, Junction-to-Ambient

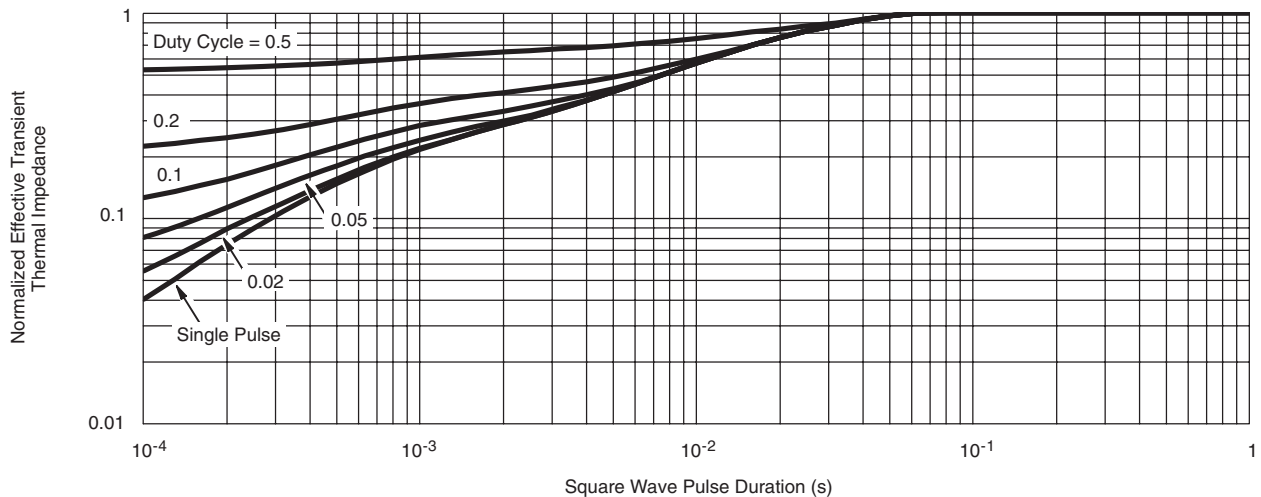
* The power dissipation P_D is based on T_{J(max)} = 175 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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